



ZXMP6A17N8TC Information



For Reference Only

Part Number ZXMP6A17N8TC
Manufacturer Diodes Incorporated

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 60V 2.7A 8SO **Package** 8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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ZXMP6A17N8TC Specifications

Manufacturer Part Number ZXMP6A17N8TC Manufacturer Diodes Incorporated Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 2.7A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250µA Gate Charge (Qg) (Max) @ Vgs 17.7n C @ 10V Input Capacitance (Ciss) (Max) @ Vds 637p F @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.56W (Ta) Rds On (Max) @ Id, Vgs 125 mOhm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		
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FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C2.7A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs17.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds637pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.56W (Ta)Rds On (Max) @ Id, Vgs125 mOhm @ 2.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C2.7A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs17.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds637pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.56W (Ta)Rds On (Max) @ Id, Vgs125 mOhm @ 2.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C2.7A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs17.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds637pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.56W (Ta)Rds On (Max) @ Id, Vgs125 mOhm @ 2.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 17.7nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 637pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 125 mOhm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs17.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds637pF @ 30VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.56W (Ta)Rds On (Max) @ Id, Vgs125 mOhm @ 2.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 17.7nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 637pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 125 mOhm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	2.7A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 637pF @ 30V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 125 mOhm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 125 mOhm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	1V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.56W (Ta)Rds On (Max) @ Id, Vgs125 mOhm @ 2.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	17.7nC @ 10V
FET Feature - Power Dissipation (Max) 1.56W (Ta) Rds On (Max) @ Id, Vgs 125 mOhm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	637pF @ 30V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 125 mOhm @ 2.3A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs125 mOhm @ 2.3A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	1.56W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	125 mOhm @ 2.3A, 10V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

ZXMP6A17N8TC Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

ZXMP6A17N8TC Payment Methods



















ZXMP6A17N8TC Shipping Methods













If you have any question about ZXMP6A17N8TC, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com